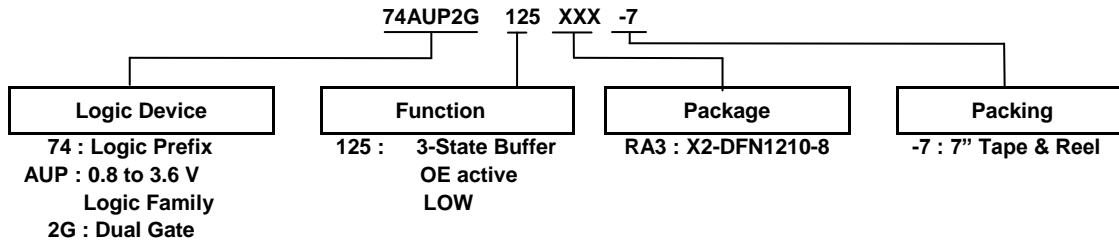


## Ordering Information



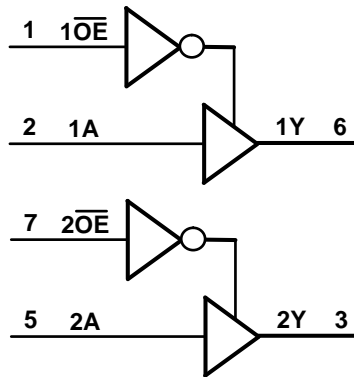
Device	Package Code	Package (Notes 4 & 5)	Package Size	7" Tape and Reel	
				Quantity	Part Number Suffix
74AUP2G125RA3-7	RA3	X2-DFN1210-8	1.2mm X 1.0 mm X 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.  
5. The taping orientation is located on our website at <http://www.diodes.com/datasheets/ap02007.pdf>

## Pin Descriptions

Pin Name	Pin NO.	Description
1 $\overline{OE}$	1	Output Enable active LOW
1A	2	Data Input
2Y	3	Data Output
GND	4	Ground
2A	5	Data Input
1Y	6	Data Output
2 $\overline{OE}$	7	Output Enable active LOW
V <sub>CC</sub>	8	Supply Voltage

## Logic Diagram



## Function Table

Inputs		Output
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

**Absolute Maximum Ratings** (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V <sub>CC</sub>	Supply Voltage Range	-0.5 to +4.6	V
V <sub>I</sub>	Input Voltage Range	-0.5 to +4.6	V
V <sub>O</sub>	Voltage Applied to Output in High or Low State	-0.5 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> < 0	50	mA
I <sub>OK</sub>	Output Clamp Current (V <sub>O</sub> < 0)	50	mA
I <sub>O</sub>	Continuous Output Current (V <sub>O</sub> = 0 to V <sub>CC</sub> )	±20	mA
I <sub>CC</sub>	Continuous Current Through V <sub>CC</sub>	50	mA
I <sub>GND</sub>	Continuous Current Through GND	-50	mA
T <sub>J</sub>	Operating Junction Temperature	-40 to +150	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

- Notes:
- Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.
  - Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

**Recommended Operating Conditions** (Note 8)

Symbol	Parameter	Min	Max	Unit		
V <sub>CC</sub>	Operating Voltage	0.8	3.6	V		
V <sub>I</sub>	Input Voltage	0	3.6	V		
V <sub>O</sub>	Output Voltage	0	V <sub>CC</sub>	V		
I <sub>OH</sub>	High-Level Output Current	V <sub>CC</sub> = 0.8V	—	-20	μA	
		V <sub>CC</sub> = 1.1V	—	-1.1	mA	
		V <sub>CC</sub> = 1.4V	—	-1.7		
		V <sub>CC</sub> = 1.65V	—	-1.9		
		V <sub>CC</sub> = 2.3V	—	-3.1		
		V <sub>CC</sub> = 3.0V	—	-4		
I <sub>OL</sub>	Low-Level Output Current	V <sub>CC</sub> = 0.8V	—	20	μA	
		V <sub>CC</sub> = 1.1V	—	1.1	mA	
		V <sub>CC</sub> = 1.4V	—	1.7		
		V <sub>CC</sub> = 1.65V	—	1.9		
		V <sub>CC</sub> = 2.3V	—	3.1		
		V <sub>CC</sub> = 3.0V	—	4		
Δt/ΔV	Input Transition Rise or Fall Rate	V <sub>CC</sub> = 0.8V to 3.6V		—	200	ns/V
T <sub>A</sub>	Operating Free-Air Temperature	-40	125	°C		

- Note: 8. Unused inputs should be held at V<sub>CC</sub> or Ground.

## Electrical Characteristics

Symbol	Parameter	Test Conditions	V <sub>CC</sub>	T <sub>A</sub> = +25°C		T <sub>A</sub> = -40°C to +85°C		Unit
				Min	Max	Min	Max	
V <sub>IH</sub>	High-Level Input Voltage	—	0.8V to 1.65V	0.80 X V <sub>CC</sub>	—	0.80 X V <sub>CC</sub>	—	V
		—	1.65V to 1.95V	0.65 X V <sub>CC</sub>	—	0.65 X V <sub>CC</sub>	—	
		—	2.3V to 2.7V	1.6	—	1.6	—	
		—	3.0V to 3.6V	2.0	—	2.0	—	
V <sub>IL</sub>	Low-Level Input Voltage	—	0.8V to 1.65V	—	0.30 X V <sub>CC</sub>	—	0.30 X V <sub>CC</sub>	V
		—	1.65V to 1.95V	—	0.35 X V <sub>CC</sub>	—	0.35 X V <sub>CC</sub>	
		—	2.3V to 2.7V	—	0.7	—	0.7	
		—	3.0V to 3.6V	—	0.9	—	0.9	
V <sub>OH</sub>	High-Level Output Voltage	I <sub>OH</sub> = -20μA	0.8V to 3.6V	V <sub>CC</sub> - 0.1	—	V <sub>CC</sub> - 0.1	—	V
		I <sub>OH</sub> = -1.1mA	1.1V	0.75 X V <sub>CC</sub>	—	0.7 X V <sub>CC</sub>	—	
		I <sub>OH</sub> = -1.7mA	1.4V	1.11	—	1.03	—	
		I <sub>OH</sub> = -1.9mA	1.65V	1.32	—	1.3	—	
		I <sub>OH</sub> = -2.3mA	2.3V	2.05	—	1.97	—	
		I <sub>OH</sub> = -3.1mA		1.9	—	1.85	—	
		I <sub>OH</sub> = -2.7mA	3V	2.72	—	2.67	—	
I <sub>OH</sub> = -4mA	2.6	—		2.55	—			
V <sub>OL</sub>	Low-Level Output Voltage	I <sub>OL</sub> = 20μA	0.8V to 3.6V	—	0.1	—	0.1	V
		I <sub>OL</sub> = 1.1mA	1.1V	—	0.3 X V <sub>CC</sub>	—	0.3 X V <sub>CC</sub>	
		I <sub>OL</sub> = 1.7mA	1.4V	—	0.31	—	0.37	
		I <sub>OL</sub> = 1.9mA	1.65V	—	0.31	—	0.35	
		I <sub>OL</sub> = 2.3mA	2.3V	—	0.31	—	0.33	
		I <sub>OL</sub> = 3.1mA		—	0.44	—	0.45	
		I <sub>OL</sub> = 2.7mA	3V	—	0.31	—	0.33	
I <sub>OL</sub> = 4mA	—	0.44		—	0.45			
I <sub>I</sub>	Input Current	A or B Input V <sub>I</sub> = GND to 3.6V	0 to 3.6V	—	± 0.1	—	± 0.5	μA
I <sub>OZ</sub>	Z-State Leakage Current	V <sub>I</sub> or V <sub>O</sub> = 0V to 3.6V	0 to 3.6V	—	0.2	—	± 0.5	μA
I <sub>OFF</sub>	Power Down Leakage Current	V <sub>I</sub> or V <sub>O</sub> = 0V to 3.6V	0 V	—	± 0.2	—	± 0.5	μA
ΔI <sub>OFF</sub>	Delta Power Down Leakage Current	V <sub>I</sub> or V <sub>O</sub> = 0V to 3.6V	0 V to 0.2V	—	0.2	—	0.6	μA
I <sub>CC</sub>	Supply Current	V <sub>I</sub> = GND or V <sub>CC</sub> , I <sub>O</sub> = 0	0.8 V to 3.6V	—	0.5	—	0.9	μA
ΔI <sub>CC</sub>	Additional Supply Current	Data Input at V <sub>CC</sub> - 0.6 V OE = GND I <sub>O</sub> = 0 A	3.3V	—	40	—	50	μA
		OE Input at V <sub>CC</sub> - 0.6 V Data Input = GND or V <sub>CC</sub> I <sub>O</sub> = 0 A	3.3V	—	110	—	120	μA
		OE Input at V <sub>CC</sub> Data Input = GND to 3.6 V I <sub>O</sub> = 0 A	0.8V to 3.6V	—	1	—	1	μA

### Electrical Characteristics (cont.)

Symbol	Parameter	Test Conditions	V <sub>CC</sub>	T <sub>A</sub> = -40°C to +125°C		Unit
				Min	Max	
V <sub>IH</sub>	High-Level Input Voltage	—	0.8V to 1.65V	0.80 X V <sub>CC</sub>	—	V
		—	1.65V to 1.95V	0.70 X V <sub>CC</sub>	—	
		—	2.3V to 2.7V	1.6	—	
		—	3.0V to 3.6V	2.0	—	
V <sub>IL</sub>	Low-Level Input Voltage	—	0.8V to 1.65V	—	0.25 X V <sub>CC</sub>	V
		—	1.65V to 1.95V	—	0.30 X V <sub>CC</sub>	
		—	2.3V to 2.7V	—	0.7	
		—	3.0V to 3.6V	—	0.9	
V <sub>OH</sub>	High-Level Output Voltage	I <sub>OH</sub> = -20μA	0.8V to 3.6V	V <sub>CC</sub> - 0.11	—	V
		I <sub>OH</sub> = -1.1mA	1.1V	0.6 X V <sub>CC</sub>	—	
		I <sub>OH</sub> = -1.7mA	1.4V	0.93	—	
		I <sub>OH</sub> = -1.9mA	1.65V	1.17	—	
		I <sub>OH</sub> = -2.3mA	2.3V	1.77	—	
		I <sub>OH</sub> = -3.1mA		1.67	—	
		I <sub>OH</sub> = -2.7mA	3V	2.40	—	
		I <sub>OH</sub> = -4mA		2.30	—	
V <sub>OL</sub>	Low-Level Output Voltage	I <sub>OL</sub> = 20μA	0.8V to 3.6V	—	0.11	V
		I <sub>OL</sub> = 1.1mA	1.1V	—	0.33 X V <sub>CC</sub>	
		I <sub>OL</sub> = 1.7mA	1.4V	—	0.41	
		I <sub>OL</sub> = 1.9mA	1.65V	—	0.39	
		I <sub>OL</sub> = 2.3mA	2.3V	—	0.36	
		I <sub>OL</sub> = 3.1mA		—	0.50	
		I <sub>OL</sub> = 2.7mA	3V	—	0.36	
		I <sub>OL</sub> = 4mA		—	0.50	
I <sub>I</sub>	Input Current	A or B Input, V <sub>I</sub> = GND to 3.6V	0 to 3.6V	—	± 0.75	μA
I <sub>OZ</sub>	Z-State Leakage Current	V <sub>I</sub> or V <sub>O</sub> = 0V to 3.6V	0 to 3.6V	—	± 1.5	μA
I <sub>OFF</sub>	Power Down Leakage Current	V <sub>I</sub> or V <sub>O</sub> = 0V to 3.6V	0	—	± 3.5	μA
ΔI <sub>OFF</sub>	Delta Power Down Leakage Current	V <sub>I</sub> or V <sub>O</sub> = 0V to 3.6V	0V to 0.2V	—	± 2.5	μA
I <sub>CC</sub>	Supply Current	V <sub>I</sub> = GND or V <sub>CC</sub> , I <sub>O</sub> = 0	0.8V to 3.6V	—	3.0	μA
ΔI <sub>CC</sub>	Additional Supply Current	Data Input at V <sub>CC</sub> - 0.6 V OE = GND I <sub>O</sub> = 0 A	3.3V	—	75	μA
		OE Input at V <sub>CC</sub> - 0.6 V Data Input = GND or V <sub>CC</sub> I <sub>O</sub> = 0 A	3.3V	—	180	μA
		OE Input at V <sub>CC</sub> Data Input = GND to 3.6 V I <sub>O</sub> = 0 A	0.8V to 3.6V	—	1	μA

**Operating and Package Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Parameter		Test Conditions		V <sub>CC</sub>	Typ	Unit
C <sub>pd</sub>	Power Dissipation Capacitance per gate	f = 1MHz Output Enabled No Load		0.8V	6.5	pF
				1.2V ± 0.1V	6.3	
				1.5V ± 0.1V	6.3	
				1.8V ± 0.15V	6.2	
				2.5V ± 0.2V	6.2	
				3.3V ± 0.3V	6.1	
C <sub>i</sub>	Input Capacitance	V <sub>i</sub> = V <sub>CC</sub> or GND		0V or 3.3V	1.5	pF
C <sub>o</sub>	Output Capacitance	Output Enabled VO=Gnd		0 V	2.9	pF
		Output Disabled VO=Gnd or Vcc		0V or 3.6V	2.1	pF
θ <sub>JA</sub>	Thermal Resistance Junction-to-Ambient	X2-DFN1210-8	(Note 9)	—	395	°C/W
θ <sub>JC</sub>	Thermal Resistance Junction-to-Case	X2-DFN1210-8	(Note 9)	—	236	°C/W

Note: 9. Test condition, X2-DFN1210-8 device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

## Switching Characteristics

C<sub>L</sub> = 5pF, See Figure 1

Parameter	From Input	To Output	V <sub>CC</sub>	T <sub>A</sub> = +25°C			T <sub>A</sub> = -40°C to +85°C		T <sub>A</sub> = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t <sub>pd</sub>	A	Y	0.8V	—	20.6	—	—	—	—	—	ns
			1.2V ± 0.1V	2.8	5.5	12.6	2.5	14.0	2.5	17	
			1.5V ± 0.1V	2.2	3.9	7.3	2.0	7.5	2.0	8.1	
			1.8V ± 0.15V	1.9	3.2	4.8	1.7	6.1	1.7	6.7	
			2.5V ± 0.2V	1.6	2.6	3.6	1.4	4.3	1.4	4.9	
t <sub>en</sub>	OE	Y	0.8V	—	69.9	—	—	—	—	—	ns
			1.2V ± 0.1V	3.1	6.1	14.2	2.9	20	2.9	22.2	
			1.5V ± 0.1V	2.5	4.2	7.9	2.3	9.2	2.3	10.0	
			1.8V ± 0.15V	2.1	3.4	6.1	2.0	7.4	2.0	8.2	
			2.5V ± 0.2V	1.8	2.6	4.4	1.7	5.4	1.7	6.0	
t <sub>dis</sub>	OE	Y	0.8V	—	14.3	—	—	—	—	—	ns
			1.2V ± 0.1V	2.7	4.3	9.4	2.7	10.6	2.7	11.8	
			1.5V ± 0.1V	2.1	3.2	6.4	2.1	7.3	2.1	8.2	
			1.8V ± 0.15V	2.0	3.0	5.5	2.0	6.3	2.0	7.1	
			2.5V ± 0.2V	1.4	2.2	3.7	1.4	4.2	1.4	5.1	
t <sub>dis</sub>	OE	Y	3.3V ± 0.3V	1.7	2.5	4.4	1.7	4.6	1.7	5.4	ns

C<sub>L</sub> = 10pF, See Figure 1

Parameter	From Input	To Output	V <sub>CC</sub>	T <sub>A</sub> = +25°C			T <sub>A</sub> = -40°C to +85°C		T <sub>A</sub> = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t <sub>pd</sub>	A	Y	0.8V	—	24.0	—	—	—	—	—	ns
			1.2V ± 0.1V	3.2	6.4	14.8	3.0	16.6	3.0	18.2	
			1.5V ± 0.1V	2.1	4.5	8.8	1.9	9.1	1.9	9.4	
			1.8V ± 0.15V	1.9	3.8	5.5	1.7	6.8	1.7	7.6	
			2.5V ± 0.2V	2.1	3.2	4.2	1.6	5.3	1.6	5.9	
t <sub>en</sub>	OE	Y	0.8V	—	73.7	—	—	—	—	—	ns
			1.2V ± 0.1V	3.6	6.9	16.2	3.4	22.8	3.4	25.2	
			1.5V ± 0.1V	2.3	4.8	9.2	2.2	10.3	2.2	11.3	
			1.8V ± 0.15V	2.0	3.9	7.0	1.9	8.2	1.9	8.9	
			2.5V ± 0.2V	1.8	3.2	5.2	1.7	6.4	1.7	7.1	
t <sub>dis</sub>	OE	Y	0.8V	—	32.7	—	—	—	—	—	ns
			1.2V ± 0.1V	3.4	5.4	11.4	3.4	12.7	3.4	14.3	
			1.5V ± 0.1V	2.2	4.1	7.9	2.2	8.9	2.2	10.2	
			1.8V ± 0.15V	2.2	4.2	7.0	1.9	8.0	1.9	8.9	
			2.5V ± 0.2V	1.7	3.0	4.8	1.7	5.7	1.7	6.4	
t <sub>dis</sub>	OE	Y	3.3V ± 0.3V	2.1	3.8	6.5	1.7	6.8	1.7	7.7	ns

**Switching Characteristics** (cont.)

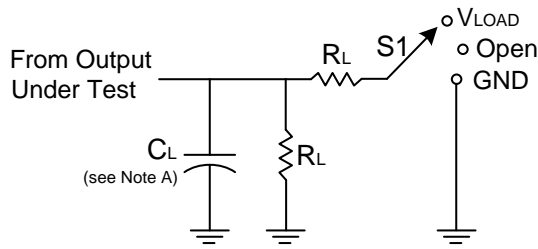
 $C_L = 15\text{pF}$ , See Figure 1

Parameter	From Input	To Output	V <sub>CC</sub>	T <sub>A</sub> = +25°C			T <sub>A</sub> = -40°C to +85°C		T <sub>A</sub> = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t <sub>pd</sub>	A	Y	0.8V	—	27.4	—	—	—	—	—	ns
			1.2V ± 0.1V	3.6	7.2	15.8	3.3	22.4	3.3	22.5	
			1.5V ± 0.1V	3.0	5.1	8.8	2.5	9.8	2.5	10.9	
			1.8V ± 0.15V	2.2	4.3	6.3	2.0	7.9	2.0	8.8	
			2.5V ± 0.2V	2.0	3.7	4.9	1.8	6.0	1.8	6.7	
			3.3V ± 0.3V	2.0	3.5	4.4	1.8	5.4	1.8	6.1	
t <sub>en</sub>	OE	Y	0.8V	—	77.5	—	—	—	—	—	ns
			1.2V ± 0.1V	4.0	7.7	18.2	3.7	21.8	3.7	23.5	
			1.5V ± 0.1V	3.0	5.3	10.1	2.5	11.8	2.5	12.8	
			1.8V ± 0.15V	2.3	4.4	7.8	2.1	9.2	2.1	10.2	
			2.5V ± 0.2V	2.1	3.6	6.0	2.0	7.3	2.0	8.2	
			3.3V ± 0.3V	2.0	3.5	5.7	1.9	6.4	1.9	7.2	
t <sub>dis</sub>	OE	Y	0.8V	—	60.8	—	—	—	—	—	ns
			1.2V ± 0.1V	4.3	6.5	13.9	3.7	15.5	3.7	15.7	
			1.5V ± 0.1V	3.0	5.0	8.8	2.5	9.7	2.5	9.8	
			1.8V ± 0.15V	3.0	5.3	8.8	2.1	10.3	2.1	10.5	
			2.5V ± 0.2V	2.1	3.8	8.2	2.0	8.4	2.0	8.6	
			3.3V ± 0.3V	2.9	5.0	8.6	1.9	9.2	1.9	9.4	

 $C_L = 30\text{pF}$ , See Figure 1

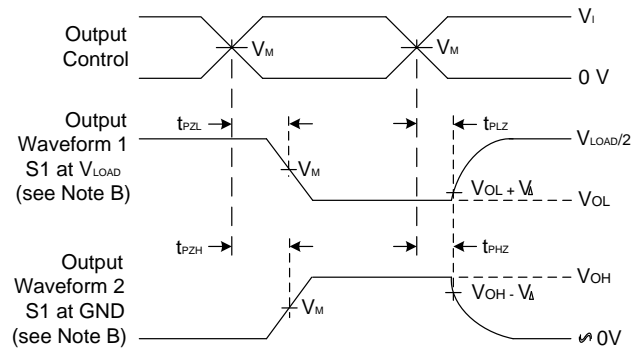
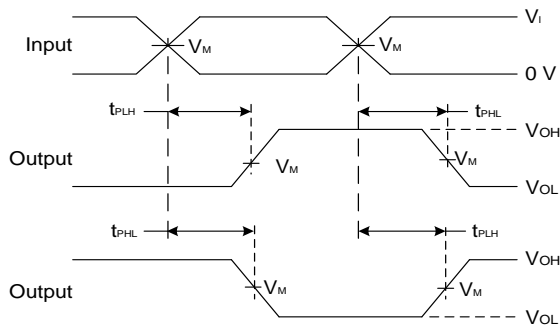
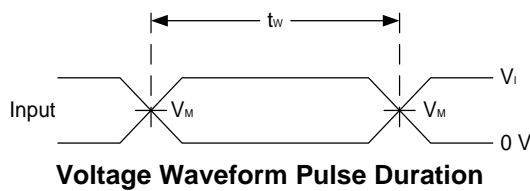
Parameter	From Input	To Output	V <sub>CC</sub>	T <sub>A</sub> = +25°C			T <sub>A</sub> = -40°C to +85°C		T <sub>A</sub> = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t <sub>pd</sub>	A	Y	0.8V	—	37.4	—	—	—	—	—	ns
			1.2V ± 0.1V	4.8	9.5	21	4.4	24.9	4.4	25	
			1.5V ± 0.1V	4.0	6.7	10.8	3.0	13.0	3.0	14.5	
			1.8V ± 0.15V	2.9	5.6	8.4	2.6	10.3	2.6	11.5	
			2.5V ± 0.2V	2.7	4.8	6.3	2.5	7.8	2.5	8.7	
			3.3V ± 0.3V	2.7	4.6	6	2.5	7.5	2.5	8.3	
t <sub>en</sub>	OE	Y	0.8V	—	88.9	—	—	—	—	—	ns
			1.2V ± 0.1V	5.2	9.9	23.8	4.8	27.4	4.8	30.4	
			1.5V ± 0.1V	4.0	6.8	13.0	3.1	15.1	3.1	16.9	
			1.8V ± 0.15V	3.0	5.6	10.2	2.8	12.2	2.8	13.6	
			2.5V ± 0.2V	2.7	4.8	7.8	2.6	9.4	2.6	10.6	
			3.3V ± 0.3V	2.7	4.6	7.8	2.6	9.0	2.6	10.0	
t <sub>dis</sub>	OE	Y	0.8V	—	49.9	—	—	—	—	—	ns
			1.2V ± 0.1V	6.0	9.9	16.0	4.8	17.8	4.8	19.8	
			1.5V ± 0.1V	4.4	7.7	11.5	3.1	13.0	3.1	14.5	
			1.8V ± 0.15V	5.1	8.7	13.3	2.8	14.9	2.8	16.6	
			2.5V ± 0.2V	3.6	6.2	9.1	2.6	10.3	2.6	11.5	
			3.3V ± 0.3V	5.2	8.7	13.7	2.6	14.0	2.6	17.0	

**Parameter Measurement Information**



TEST	S1	$R_L$
$t_{PLH}/t_{PHL}$	Open	1M $\Omega$
$t_{PLZ}/t_{PZL}$	Vload	5K $\Omega$
$t_{PHZ}/t_{PZH}$	GND	5K $\Omega$

$V_{CC}$	Inputs		$V_M$	$V_{LOAD}$	$C_L$	$V_{\Delta}$
	$V_I$	$t_r/t_f$				
0.8V	$V_{CC}$	$\leq 3ns$	$V_{CC}/2$	$2 \times V_{CC}$	5, 10, 15, 30pF	0.1 V
1.2V $\pm$ 0.1V	$V_{CC}$	$\leq 3ns$	$V_{CC}/2$	$2 \times V_{CC}$	5, 10, 15, 30pF	0.1 V
1.5V $\pm$ 0.1V	$V_{CC}$	$\leq 3ns$	$V_{CC}/2$	$2 \times V_{CC}$	5, 10, 15, 30pF	0.1 V
1.8V $\pm$ 0.15V	$V_{CC}$	$\leq 3ns$	$V_{CC}/2$	$2 \times V_{CC}$	5, 10, 15, 30pF	0.15 V
2.5V $\pm$ 0.2V	$V_{CC}$	$\leq 3ns$	$V_{CC}/2$	$2 \times V_{CC}$	5, 10, 15, 30pF	0.15 V
3.3V $\pm$ 0.3V	$V_{CC}$	$\leq 3ns$	$V_{CC}/2$	$2 \times V_{CC}$	5, 10, 15, 30pF	0.3V



**Figure 1 Load Circuit and Voltage Waveforms**


- Notes:
- A. Includes test lead and test apparatus capacitance.
  - B. All pulses are supplied at pulse repetition rate  $\leq 10$  MHz.
  - C. Inputs are measured separately one transition per measurement.
  - D.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - E.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{EN}$ .
  - F.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD}$ .



**Marking Information**

X2-DFN1210-8

( Top View )

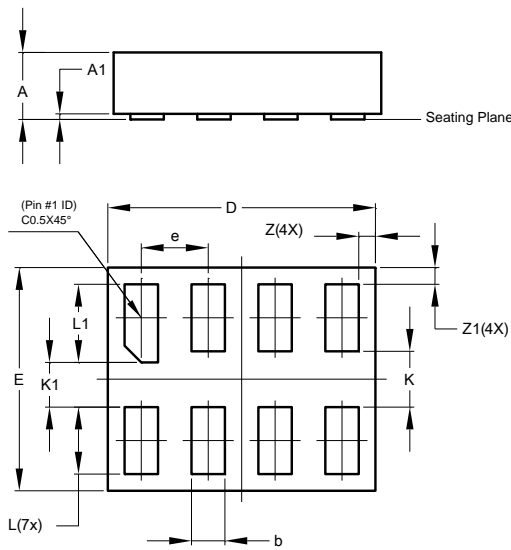


XX : Identification Code  
Y : Year : 0~9  
W : week : A~Z : 1~26 week  
           a~z: 27-52 week  
           z represents 52 and 53 week  
X : week : A~Z : Internal code

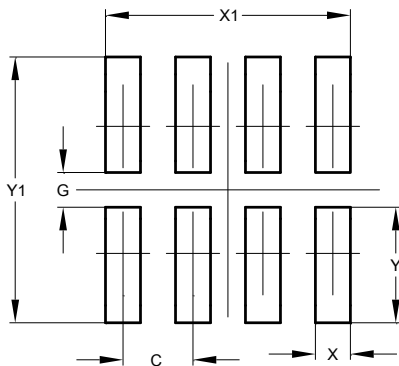
Part Number	Package	Identification Code
74AUP2G125RA3-7	X2-DFN1210-8	JT

**X2-DFN1210-8 Package Outline Dimensions and Suggested Pad Layout**

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



X2-DFN1210-8			
Dim	Min	Max	Typ
A	-	0.35	0.30
A1	0	0.03	0.02
b	0.10	0.20	0.15
D	1.15	1.25	1.20
E	0.95	1.05	1.00
e	-	-	0.30
K	-	-	0.25
K1	-	-	0.20
L	0.25	0.35	0.30
L1	0.30	0.40	0.35
Z	0.050	0.100	0.075
Z1	0.050	0.100	0.075
All Dimensions in mm			



Dimensions	Value (in mm)
C	0.300
G	0.150
X	0.150
X1	1.050
Y	0.500
Y1	1.150

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